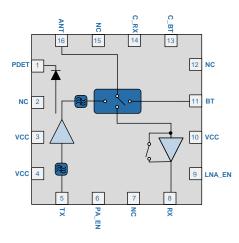


RFFM8202

2.4GHz to 2.5GHz 802.11b/g/n WiFi Front End Module

The RFFM8202 provides a complete integrated solution in a single front end module (FEM) for WiFi 802.11b/g/n and Bluetooth® systems. The ultra small form factor and integrated matching greatly reduces the number of external components and layout area in the customer application. This simplifies the total front end solution by reducing the bill of materials, system footprint, and manufacturability cost. The RFFM8202 integrates a 2.4GHz to 2.5GHz power amplifier (PA), low noise amplifier (LNA) with bypass mode, power detector coupler for improved accuracy, SP3T switch, and some filtering for harmonic rejection. The device is provided in 2.5mm x 2.5mm x 0.45mm 16-pin QFN package. This module meets or exceeds the RF front end needs of IEEE 802.11b/g/n WiFi RF systems.



● rfmd 》》 RFFM8202

Package: QFN, 16-pin, 2.5mm x 2.5mm x 0.45

Features

- P_{OUT} = 19dBm 11g OFDM 2.5%
 EVM
- P_{OUT} = 21dBm Meeting 11b Spec Mask
- Voltage Range 3.0V to 4.8V
- Input and Output Matched to 50Ω; High Level of Integration
- Supports Wide Voltage Supply Range

Applications

- Cellular Handsets
- Mobile Devices
- Tablets
- Consumer Electronics
- Gaming
- Netbooks/Notebooks
- TV/Monitors/Video
- Smart Energy

Functional Block Diagram

Ordering Information

| or doring intornia | | | | |
|--------------------|---|--|--|--|
| RFFM8202SB | Standard 5 piece sample bag | | | |
| RFFM8202SQ | Standard 25 piece sample bag | | | |
| RFFM8202SR | Standard 100 piece reel | | | |
| RFFM8202TR7 | Standard 2500 piece reel | | | |
| RFFM8202PCK-410 | Fully assembled eval board w/5-piece sample bag | | | |

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Absolute Maximum Ratings

| Parameter | Rating | Unit |
|---|-------------|------|
| DC Supply Voltage (No RF Applied) | 6 | V |
| DC Supply Current | 500 | mA |
| Operating Temperature Range | -40 to +85 | °C |
| Storage Temperature | -40 to +150 | °C |
| Maximum TX Input Power into 50 W Load for 11b/g/n (No Damage) | +10 | dBm |
| Maximum RX input power for both LNA_EN mode and bypass mode (No damage) | +10 | dBm |
| Moisture Sensitivity | MSL1 | |



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RFMD Green: RoHS status based on EU Directive 2011/65/EU (at time of this document revision), halogen free per IEC 61249-2-21, < 1000ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

Nominal Operating Parameters

| Deremeter | Specification | | | | | |
|---------------------------------------|---------------|-----|-------|------|--|--|
| Parameter | Min | Тур | Max | Unit | Condition | |
| | | | | | | |
| Operating Range | 2.412 | | 2.484 | GHz | | |
| Operating Temperature | -40 | 25 | +85 | °C | | |
| Power Supply V _{cc} | 3.0 | 3.3 | 4.35 | V | Recommended Operating Voltage Range | |
| Extended V _{cc} | | | 4.8 | V | Functional with derated performance | |
| Control Voltage-High | 2.8 | 3.1 | Vcc | V | PA_EN, C_RX, C_BT, LNA_EN. | |
| Control Voltage-Low | 0 | | 0.2 | V | | |
| Transmit (TX-ANT) | | | | | P _{OUT} = 19dBm; T = 25°C; V _{CC} = 3.3V; PA_EN = High, C_RX = C_BT = Low; Freq = 2.412GHz to 2.484GHz, measured with a standard IEEE802.11g waveform, unless otherwise noted | |
| Dynamic EVM - Nominal | | 2.5 | 3 | % | P _{OUT} = 19dBm; T = 25°C; V _{CC} = 3.3V | |
| | | -32 | -30.5 | dB | | |
| Dynamic EVM | | 2.5 | 3 | % | P _{OUT} = 16.5dBm, T = -40°C to +85°C, V _{CC} = 3.0V to 4.8V | |
| | | -32 | -30.5 | dB | | |
| Output power meeting Spectral Mask | | 21 | 22 | dBm | 11 Mbps CCK, +/- 11MHz offset from carrier | |
| TX Port Return Loss | 8 | 10 | | dB | T = -40°C to +85°C, V _{CC} = 3.0V to 4.8V | |
| ANT Port Return Loss | 10 | 12 | | dB | | |
| Nominal Gain | 23 | 25 | 28 | dB | $T = 25^{\circ}C, V_{CC} = 3.3V$ | |
| Gain | 20.5 | 25 | 29 | dB | T = -40°C to +85°C, V _{CC} = 3.0V to 4.8V | |
| Gain Flatness - 20 MHz Channel | -0.5 | | 0.5 | dB | | |
| Gain Flatness - 40 MHz Channel | -0.75 | | 0.75 | dB | | |
| Gain Flatness - 100 MHz Band | -1 | | 1 | dB | | |
| Out of Band Rejection | 4 | 7 | | dBc | 2110MHz to 2170MHz, T = 25°C, V _{CC} = 3.3V, frequency = 2.412GHz | |
| Nominal Operating Current | | 200 | 240 | mA | P _{OUT} = 19dBm; T = 25°C; V _{CC} = 3.3V | |
| Operating Current | | 200 | 230 | mA | $P_{OUT} = 16.5 dBm; T = -40^{\circ}C \text{ to } +85^{\circ}C, V_{CC} = 3.0 \text{V to } 4.8 \text{V}$ | |
| Quiescent Current | | 135 | 200 | mA | T = -40°C to +85°C, V _{CC} = 3.0V to 4.8V | |
| PA_EN Current | | 30 | 50 | μA | | |
| Leakage Current | | 1 | 10 | μA | V _{CC} = 4.8V, RF OFF | |

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| Deveneter | Specification | | | Unit | Constitution | |
|--|---------------|------|-------|---------|--|--|
| Parameter | Min | Тур | Max | Unit | Condition | |
| Transmit (TX-ANT) (continued) | | | | | P _{OUT} = 19dBm; T = 25°C; V _{CC} = 3.3V; PA_EN = High, C_RX = C_BT = Low; Freq = 2.412GHz to 2.484GHz, measured with a standard IEEE802.11g waveform, unless otherwise noted | |
| Second Harmonic | | -23 | -15 | dBm/MHz | $T = -40^{\circ}C$ to +85°C, $V_{CC} = 3.0V$ to 4.8V | |
| Third Harmonic | | -50 | -35 | dBm/MHz | | |
| Power Detector Voltage | 0.1 | 0.15 | 0.2 | V | $P_{OUT} = 0dBm$, T = -40°C to +85°C, $V_{CC} = 3.0V$ to 4.8V | |
| Power Detector Voltage | 1.0 | 1.25 | 1.5 | V | $P_{OUT} = 22dBm$, T = -40°C to +85°C, $V_{CC} = 3.0V$ to 4.8V | |
| Variation from 0-360 degree load pull | -1.5 | | 1.5 | dB | 3:1 VSWR | |
| 2.4GHz Receive Parameters | | | | | T = 25⁰C; V _{CC} = 3.3V, LNA_EN = High, C_RX = High, C_BT = Low, PA_EN = Low | |
| Compliance | | | | | IEEE802.11b/g/n, FCC CFG 15.247,.205,.209, EN, and JDEC | |
| Frequency Range | 2.412 | | 2.484 | GHz | | |
| LNA Voltage Supply | 3.0 | 3.3 | 4.8 | V | LNA V _{DD} tied to VBATT at all times | |
| LNA Current Supply | | 8 | 12 | mA | T = 25°C | |
| | | 8 | 14 | mA | $T = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = 3.0V$ to $4.8V$ | |
| LNA_EN Current | | 60 | 100 | μA | | |
| Gain | | | | | | |
| Receive | 10 | 13 | 15 | dB | LNA ON; $V_{CC} = 3.3V$; T = 25°C | |
| | 8 | 13 | 16 | dB | $T = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = 3.0V$ to $4.8V$ | |
| Bypass Mode | -14 | -10 | -7.5 | dB | T = 25°C , LNA Low, C_RX = High, C_BT = Low, PA_EN = Low | |
| | -14.5 | -10 | -7 | dB | T = -40°C to +85°C, V_{CC} = 3.0V to 4.8V, LNA_EN = Low, C_RX = High, C_BT = Low, PA_EN = Low | |
| Noise Figure | | 2 | 3 | dB | | |
| | | | 4 | | $T = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = 3.0V$ to $4.8V$ | |
| Input IP3 | -7 | 2 | | dBm | $T = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = 3.0V$ to $4.8V$ | |
| Input P1dB | -12 | -5 | | dBm | | |
| Output Return Loss | 8.5 | 10 | | dB | | |
| Input Return Loss | 4 | 5 | | dB | | |
| Bluetooth TX/RX | | | | | T = 25⁰C; V _{CC} = 3.3V, LNA_EN = Low, C_RX = Low, C_BT = High, PA_EN = Low | |
| Input / Output Power | 20 | | | dBm | T = -40°C to +85°C, V _{CC} = 3.0V to 4.8V | |
| Insertion Loss | | 0.5 | 1.2 | dB | | |
| BT Port Return Loss | 10 | 18 | | dB | | |
| ANT Port Return Loss | 10 | 18 | | dB | | |
| Isolation | | | | | | |
| TX to RX | 29 | 35 | | dB | In Tx Mode (measured from ANT to RX port) | |
| BT to RX | 24 | 27 | | dB | In BT Mode (measured from ANT to RX port) | |
| TX to BT | 9 | 18 | | dB | In Tx Mode (measured from ANT to BT port) | |
| RX to BT | 17 | 25 | | dB | In Rx High Gain Mode (measured from ANT to BT port) | |
| RX to BT (Bypass mode) | 17 | 20 | | dB | In Rx Bypass Mode (measured from ANT to BT port) | |

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| Parameter | Specification | | | Unit | |
|--|---------------|------|-----|------|-----------------|
| | Min | Тур | Max | Onit | Condition |
| General Specifications | | | | | |
| Switch Control Current – High Each Line | | 5 | 60 | μA | |
| Switch Control Current - Low Each Line | | 0.5 | 10 | μA | |
| Switching Speed | | 100 | | nS | |
| ESD HBM | | 1000 | | V | EIA/JESD22-A114 |
| ESD CDM | | 1000 | | V | JESD22-C101 |
| PA Turn-on Time | | 200 | 500 | nS | 10% to 90% |

Switch Control Logic Truth Table

| Operating Mode | PA_EN | LNA_EN | C_RX | C_BT |
|-----------------------|-------|--------|------|------|
| Standby | Low | Low | Low | Low |
| 802.11b/g/n Tx | High | Low | Low | Low |
| 802.11b/g/n Rx Gain | Low | High | High | Low |
| 802.11b/g/n Rx Bypass | Low | Low | High | Low |
| BT RX/TX | Low | Low | Low | High |

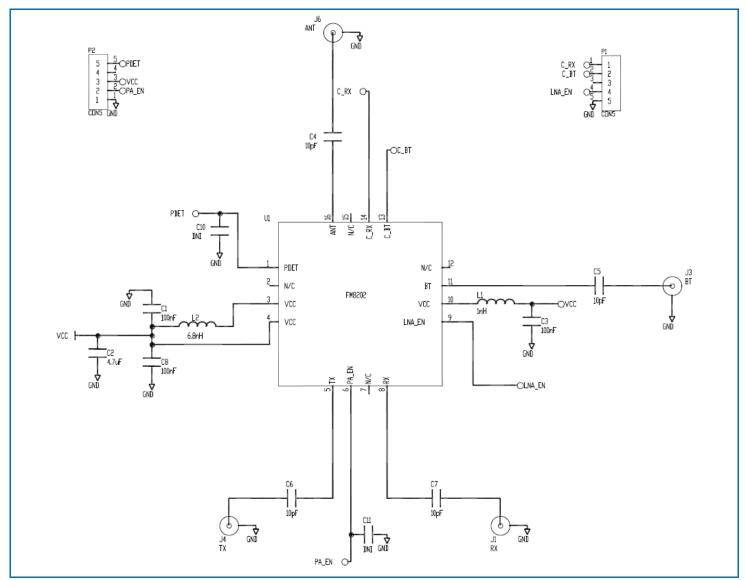
Note:

• PA_EN and TX switch control are tied together internally

• High = 2.8V to V_{CC} , Low = 0V to 0.2V



Evaluation Board Schematic

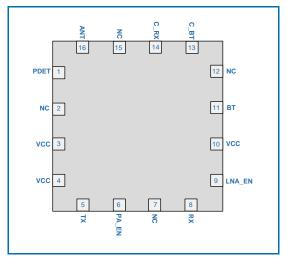


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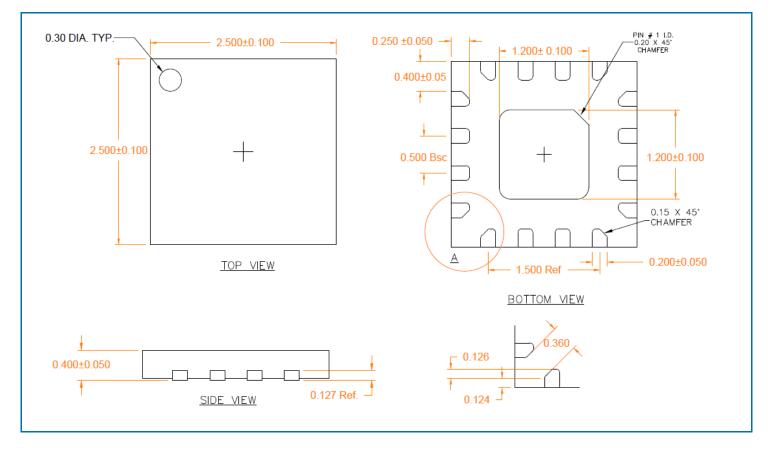
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Pin Out



Package Outline and Branding Drawing

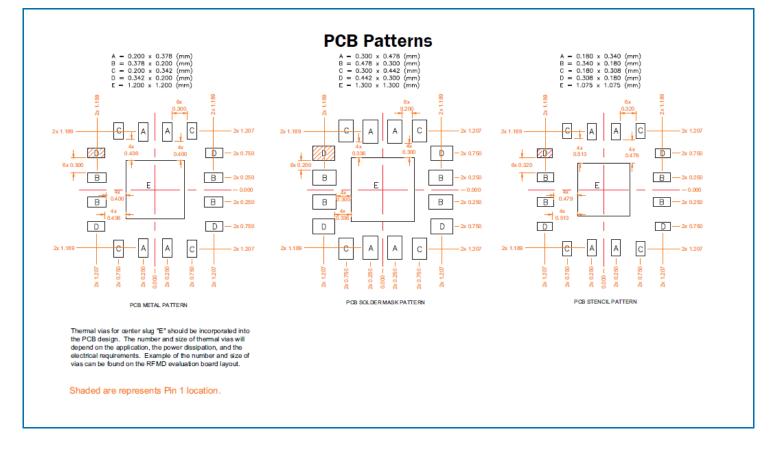


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PCB Patterns



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Pin Names and Descriptions

| Pin | Name | Description |
|----------|--------|---|
| 1 | PDET | Power detector voltage for the TX path. May need external series R and/or shunt C to adjust voltage level and to filter RF noise |
| 2 | NC* | No Connect. This pin is not connected internally and can be left floating or connected to ground. |
| 3 | VCC | Supply voltage for the output stage of the PA. See applications schematic for biasing and bypassing components. |
| 4 | VCC | Supply voltage for the first stage of the PA. See applications schematic for biasing and bypassing components. |
| 5 | тх | RF input port for the 802.11b/g/n PA. Input is matched to 50Ω . An external DC block is required. |
| 6 | PA_EN | Bias voltae for the PA. This pin also controls the TX switch of the SP3T. See truth table for proper settings. |
| 7 | NC* | No Connect. This pin is not connected internally and can be left floating or connected to ground. |
| 8 | RX | RF output port for the 802.11b/g/n LNA. Port is matched to 50Ω . An external DC block is required. |
| 9 | LNA_EN | Control voltage for the LNA. When this pin is set to a LOW logic state, the bypass mode is enabled. |
| 10 | VCC | Supply voltage for the LNA. See applications schematic for biasing and bypassing components. |
| 11 | BT | RF bidirectional port for Bluetooth®. Input is matched to 50Ω. An external DC block is required. |
| 12 | NC* | No Connect. This pin is not connected internally and can be left floating or connected to ground. |
| 13 | C_BT | Bluetooth® switch control pin. See truth table for proper level. |
| 14 | C_RX | Receive switch control pin. See switch truth table for proper level. |
| 15 | NC* | No Connect. This pin is not connected internally and can be left floating or connected to ground. |
| 16 | ANT | RF bidirectional antenna port matched to 50Ω . An external DC block is required. |
| Pkg Base | GND | Ground connection. The backside of the package should be connected to the ground plane through a short path, i.e., PCB vias under the device are recommended. |